

SILICON EPIBASE PNP DARLINGTON TRANSISTOR BDS21

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise stated)

Symbols	Parameters	Test Conditions	Min.	Typ	Max.	Units
I _{CBO}	Collector-Cut-Off Current	V _{CB} = -80V I _E = 0			-0.2	mA
		V _{CB} = -60V I _E = 0 T _C = 150°C			-1.0	
I _{CEO}	Collector-Cut-Off Current	V _{CE} = -40V I _B = 0			-0.5	
I _{EBO}	Emitter-Cut-Off Current	V _{EB} = -5V I _C = 0			-2	
h _{FE} ⁽¹⁾	Forward-current transfer ratio	I _C = -0.5A V _{CE} = -3V	1000			
		I _C = -3A V _{CE} = -3V	1000			
V _{CE(sat)} ⁽¹⁾	Collector-Emitter Saturation Voltage	I _C = -3A I _B = -12mA			-2	V
		I _C = -5A I _B = -20mA			-4	
V _{BE(sat)} ⁽¹⁾	Base-Emitter Saturation Voltage	I _C = -5A I _B = -20mA			-2.8	
V _{BE(on)} ⁽¹⁾	Base-Emitter On Voltage	I _C = -3A V _{CE} = -3V			-3.5	

DYNAMIC CHARACTERISTICS

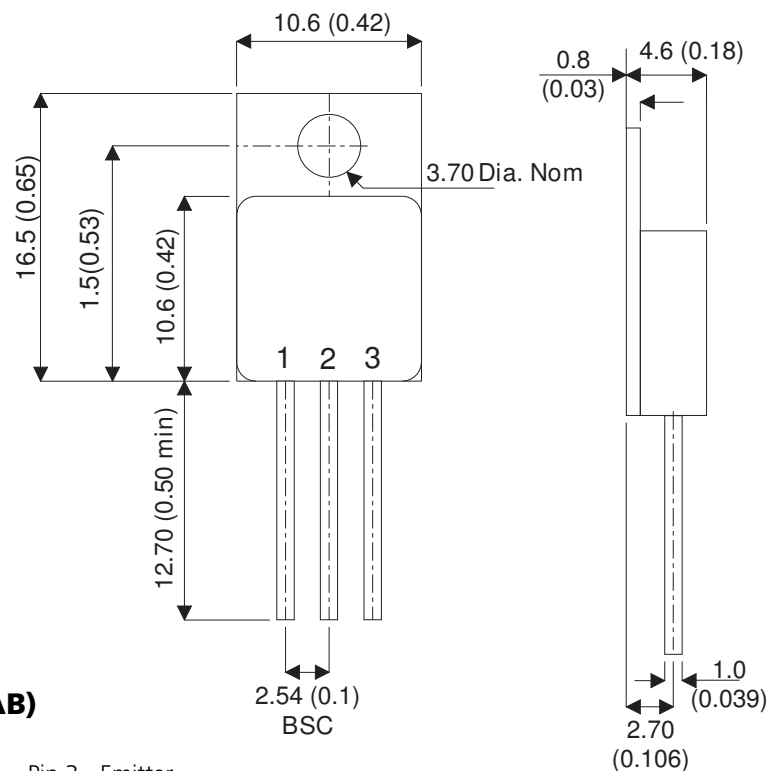
f _T	Transition Frequency	I _C = -0.5A V _{CE} = -4V f = 2MHz	8			MHz
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Notes

(1) Pulse Width ≤ 300us, δ ≤ 2%

MECHANICAL DATA

Dimensions in mm (inches)



TO220M(TO-257AB)

Pin 1 – Base

Pin 2 – Collector

Pin 3 - Emitter

Mouser Electronics

Authorized Distributor

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